

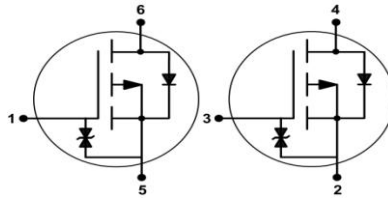
## OptiMOS™ P3 Small-Signal-Transistor

### Features

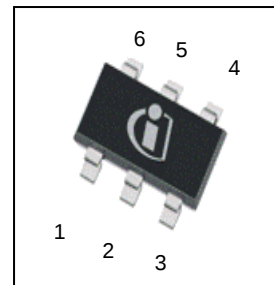
- Dual P-channel
- Enhancement mode
- Logic level (4.5V rated)
- ESD protected
- Qualified according to AEC Q101
- 100% Lead-free; RoHS compliant
- Halogen free according to IEC61249-2-21



Halogen-Free



PG-TSOP-6



| Type     | Package   | Tape and Reel Information | Marking | Lead Free | Packing |
|----------|-----------|---------------------------|---------|-----------|---------|
| BSL308PE | PG-TSOP-6 | H6327: 3000 pcs/ reel     | sPR     | Yes       | Non dry |

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter <sup>1)</sup>             | Symbol            | Conditions                                                                                                         | Value          | Unit              |
|-------------------------------------|-------------------|--------------------------------------------------------------------------------------------------------------------|----------------|-------------------|
| Continuous drain current            | $I_D$             | $T_A=25\text{ °C}$                                                                                                 | -2.0           | A                 |
|                                     |                   | $T_A=70\text{ °C}$                                                                                                 | -1.6           |                   |
| Pulsed drain current                | $I_{D,pulse}$     | $T_A=25\text{ °C}$                                                                                                 | -8.0           |                   |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=-2\text{ A}$ , $R_{GS}=25\text{ }\Omega$                                                                      | -10.7          | mJ                |
| Reverse diode $dv/dt$               | $dv/dt$           | $I_D=-2\text{ A}$ ,<br>$V_{DS}=-16\text{ V}$ ,<br>$di/dt=-200\text{ A}/\mu\text{s}$ ,<br>$T_{j,max}=150\text{ °C}$ | 6              | kV/ $\mu\text{s}$ |
| Gate source voltage                 | $V_{GS}$          |                                                                                                                    | $\pm 20$       | V                 |
| Power dissipation <sup>2)</sup>     | $P_{tot}$         | $T_A=25\text{ °C}$                                                                                                 | 0.5            | W                 |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |                                                                                                                    | -55 ... 150    | °C                |
| ESD Class                           |                   | JESD22-A114 -HBM                                                                                                   | 2 (2kV to 4kV) |                   |
| Soldering Temperature               |                   |                                                                                                                    | 260 °C         | °C                |
| IEC climatic category; DIN IEC 68-1 |                   |                                                                                                                    | 55/150/56      | °C                |

<sup>1)</sup> Only one of both transistors in operation

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                           |            |                                 |   |   |     |     |
|-------------------------------------------|------------|---------------------------------|---|---|-----|-----|
| Thermal resistance,<br>junction - ambient | $R_{thJA}$ | minimal footprint <sup>2)</sup> | - | - | 250 | K/W |
|-------------------------------------------|------------|---------------------------------|---|---|-----|-----|

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |                                             |      |      |      |           |
|----------------------------------|---------------|---------------------------------------------|------|------|------|-----------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-250\mu A$                  | -30  | -    | -    | V         |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=-11\mu A$               | -2.0 | -1.5 | -1.0 |           |
| Drain-source leakage current     | $I_{DSS}$     | $V_{DS}=-30V, V_{GS}=0V, T_j=25\text{ °C}$  | -    | -    | -1   | $\mu A$   |
|                                  |               | $V_{DS}=-30V, V_{GS}=0V, T_j=150\text{ °C}$ | -    | -    | -100 |           |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=-20V, V_{DS}=0V$                    | -    | -    | -5   | $\mu A$   |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=-4.5V, I_D=-1.7A$                   | -    | 88   | 130  | $m\Omega$ |
|                                  |               | $V_{GS}=-10V, I_D=-2A$                      | -    | 62   | 80   |           |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=-1.6A$   |      | 4.6  | -    | S         |

<sup>2)</sup> Performed on 40mm<sup>2</sup> FR4 PCB. The traces are 1mm wide, 70μm thick and 20mm long; they are present on both sides of the PCB.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Dynamic characteristics

|                              |              |                                                                                                  |   |      |     |    |
|------------------------------|--------------|--------------------------------------------------------------------------------------------------|---|------|-----|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V},$<br>$V_{DS}=-15\text{ V}, f=1\text{ MHz}$                                    | - | 376  | 500 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                                  | - | 196  | 261 |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                                  | - | 12   | 18  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=-15\text{ V},$<br>$V_{GS}=-10\text{ V},$<br>$I_D=-2\text{ A}, R_{G,ext}=6\text{ }\Omega$ | - | 5.6  | -   | ns |
| Rise time                    | $t_r$        |                                                                                                  | - | 7.7  | -   |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                                  | - | 15.3 | -   |    |
| Fall time                    | $t_f$        |                                                                                                  | - | 2.8  | -   |    |

#### Gate Charge Characteristics

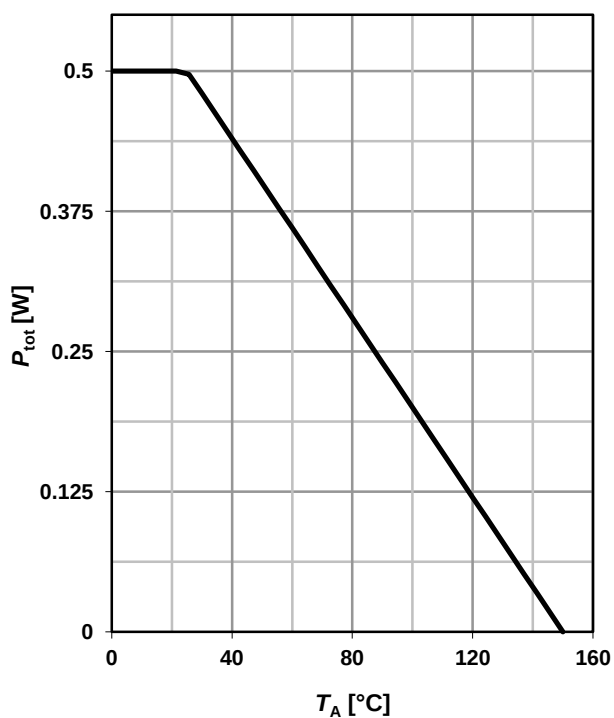
|                       |               |                                                                              |   |      |   |    |
|-----------------------|---------------|------------------------------------------------------------------------------|---|------|---|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=-15\text{ V}, I_D=-2\text{ A},$<br>$V_{GS}=0\text{ to }-10\text{ V}$ | - | -1.2 | - | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                              | - | -0.6 | - |    |
| Gate charge total     | $Q_g$         |                                                                              | - | -5.0 | - |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                              | - | -3.1 | - | V  |

#### Reverse Diode

|                                  |               |                                                                            |   |      |      |    |
|----------------------------------|---------------|----------------------------------------------------------------------------|---|------|------|----|
| Diode continuous forward current | $I_S$         | $T_A=25\text{ }^\circ\text{C}$                                             | - | -    | -0.4 | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                            | - | -    | -8.4 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=-2\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$    | - | -0.8 | -1.1 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=-10\text{ V}, I_F=-2\text{ A},$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 14   | -    | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                            | - | -5.9 | -    | nC |

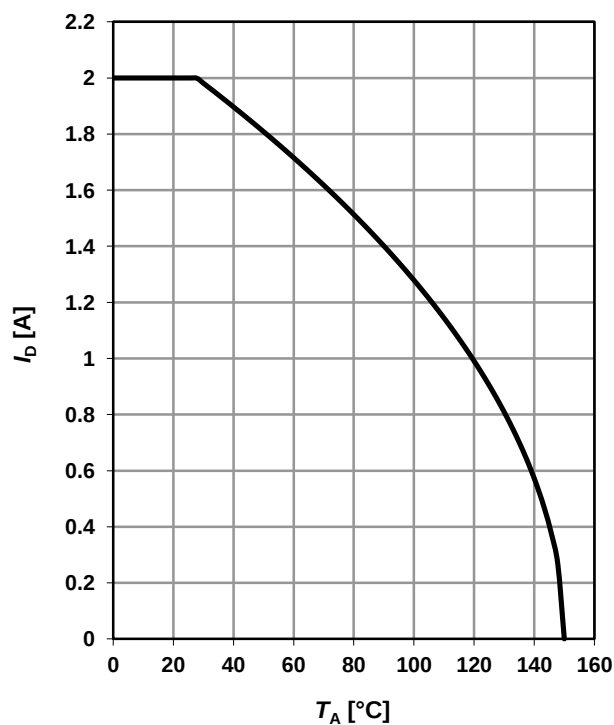
## 1 Power dissipation

$$P_{\text{tot}} = f(T_A)$$



## 2 Drain current

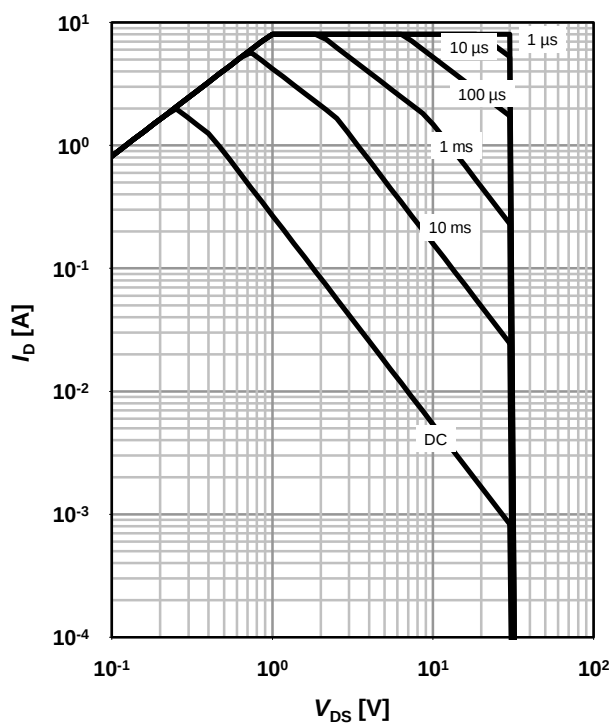
$$I_D = f(T_A); V_{GS} \geq -10 \text{ V}$$



## 3 Safe operating area

$$I_D = f(V_{DS}); T_A = 25^\circ\text{C}; D = 0$$

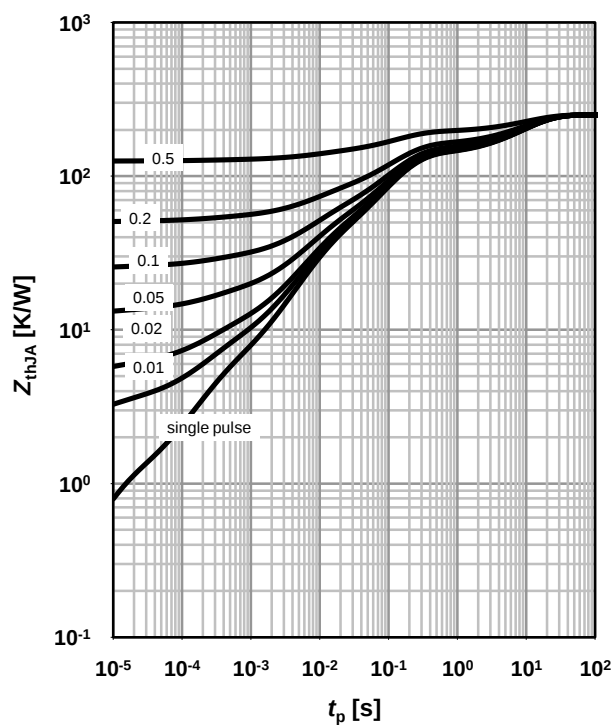
parameter:  $t_p$



## 4 Max. transient thermal impedance

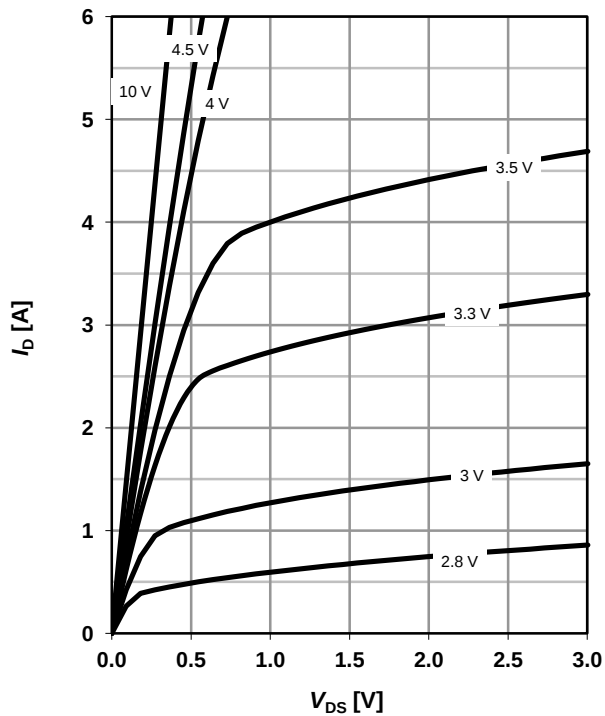
$$Z_{\text{thJA}} = f(t_p)$$

parameter:  $D = t_p/T$



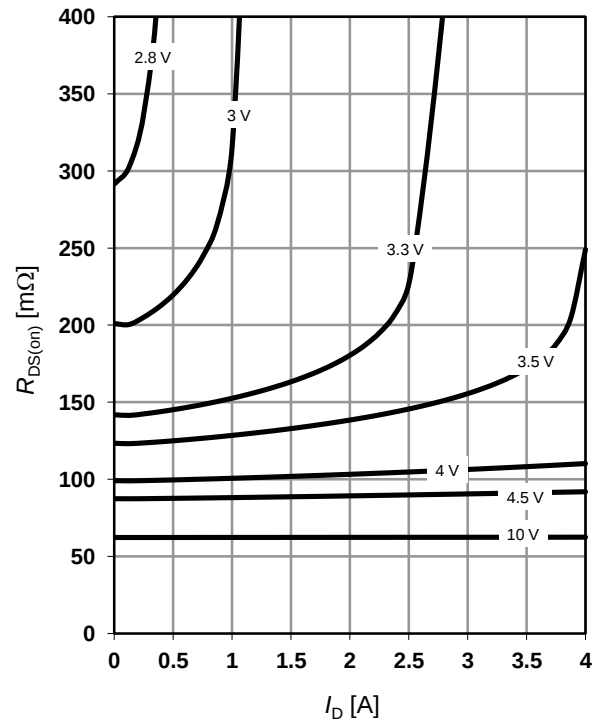
### 5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$ 

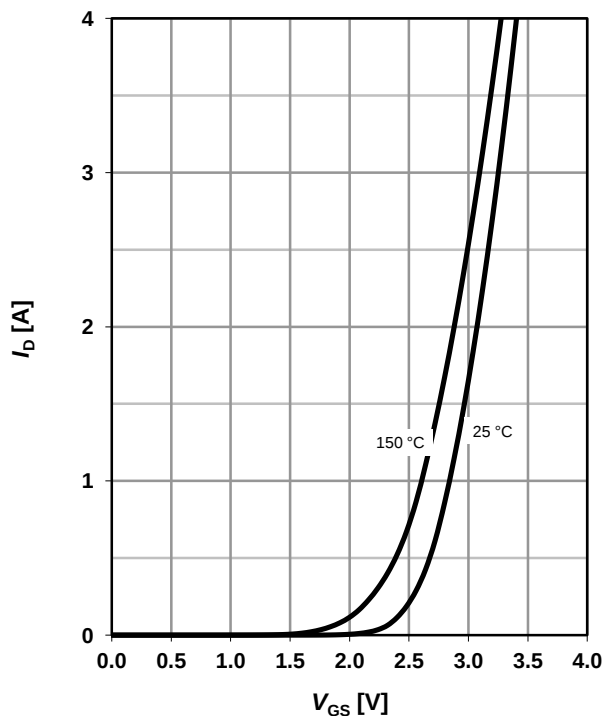
parameter:  $V_{GS}$ 


### 6 Typ. drain-source on resistance

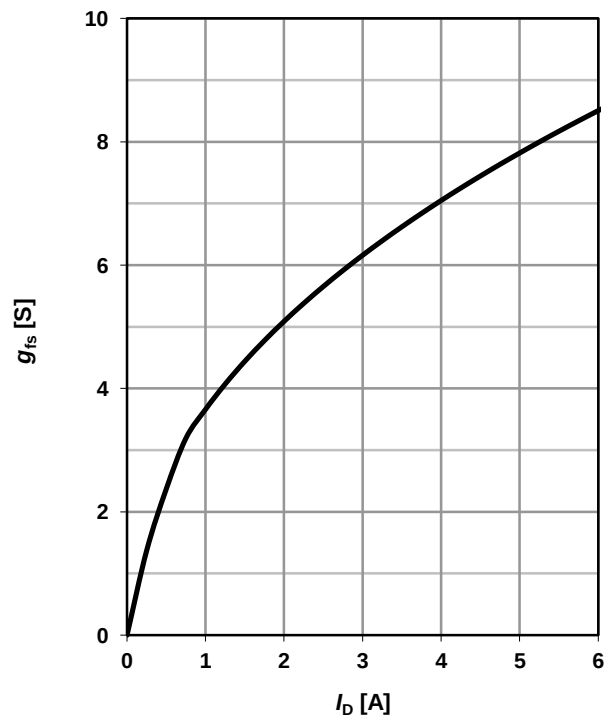
 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$ 

parameter:  $V_{GS}$ 


### 7 Typ. transfer characteristics

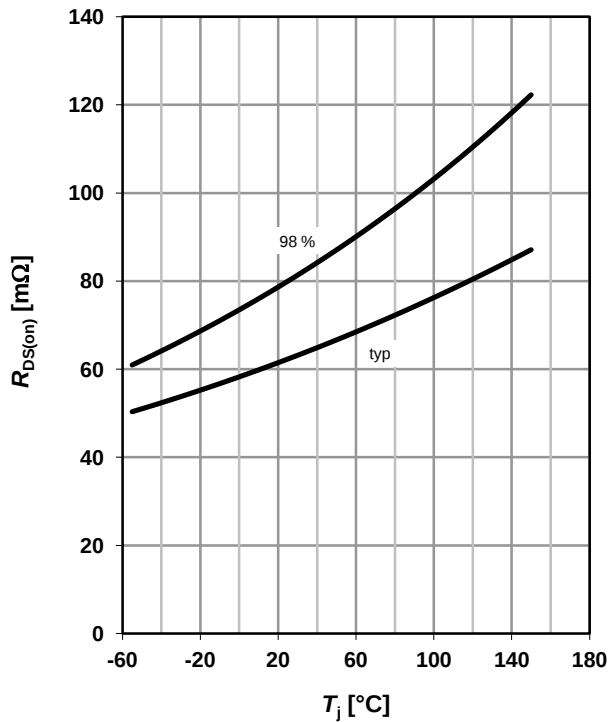
 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$ 


### 8 Typ. forward transconductance

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$ 


## 9 Drain-source on-state resistance

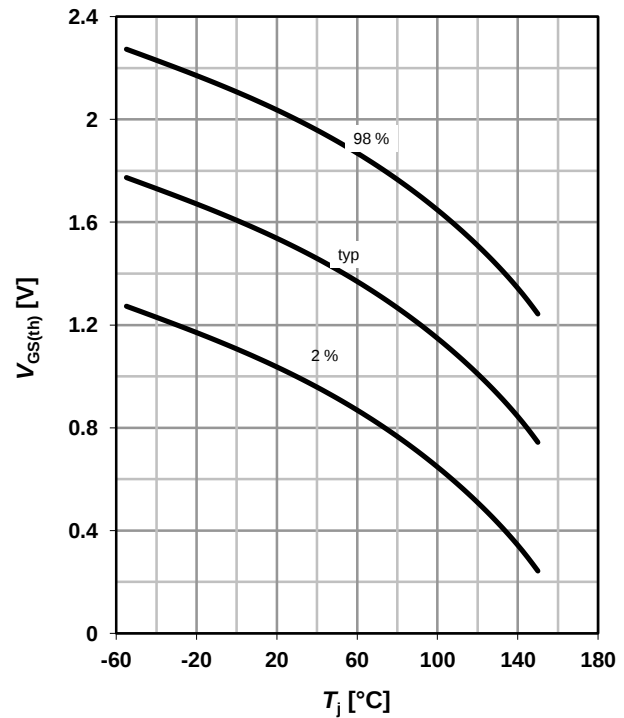
$$R_{DS(on)} = f(T_j); I_D = -2 \text{ A}; V_{GS} = -10 \text{ V}$$



## 10 Typ. gate threshold voltage

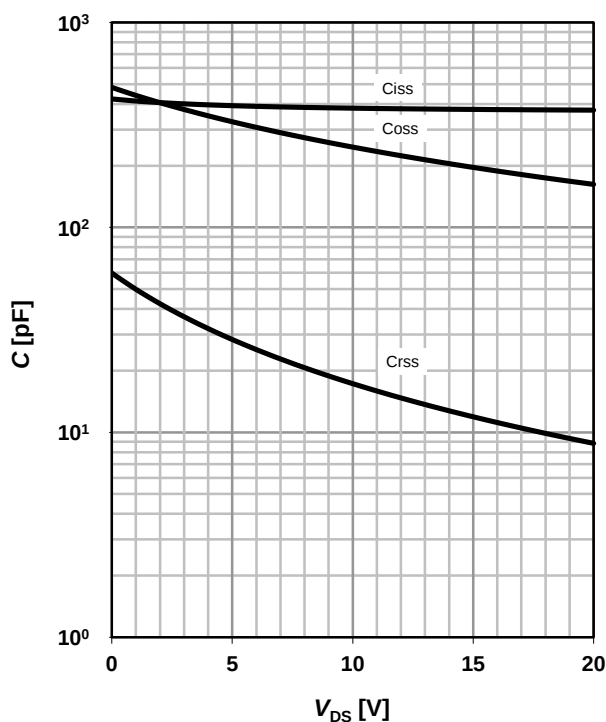
$$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 11 \mu\text{A}$$

parameter:  $I_D$



## 11 Typ. capacitances

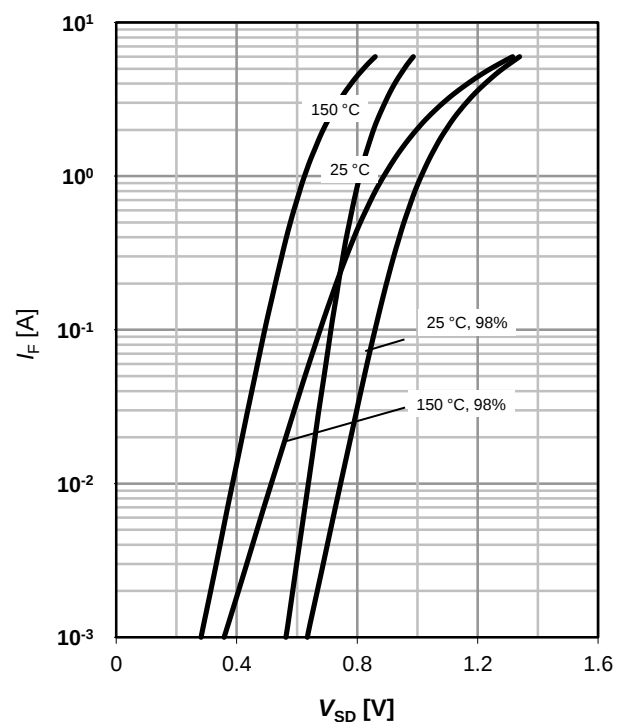
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$$



## 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

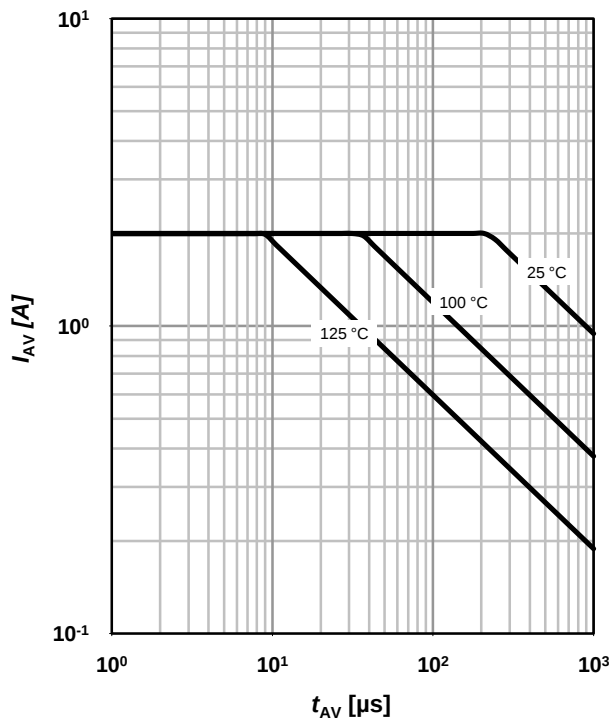
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

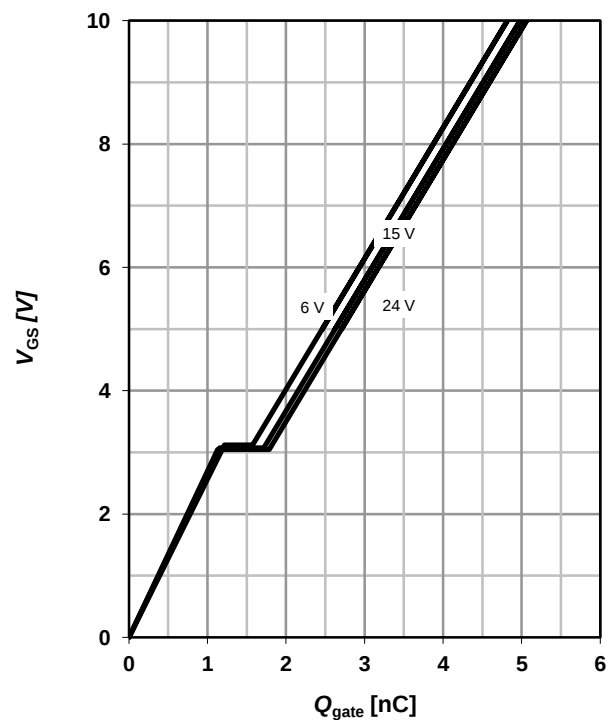
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

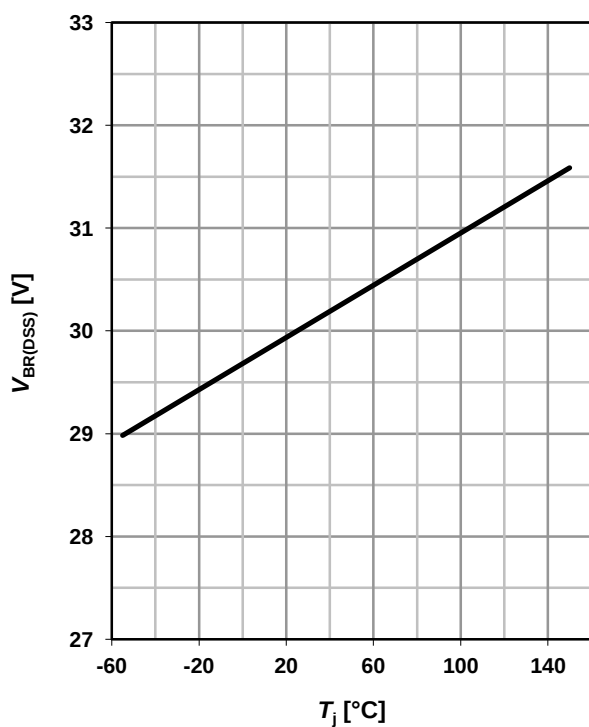
$$V_{GS}=f(Q_{\text{gate}}); I_D=-2\ \text{A pulsed}$$

parameter:  $V_{DD}$

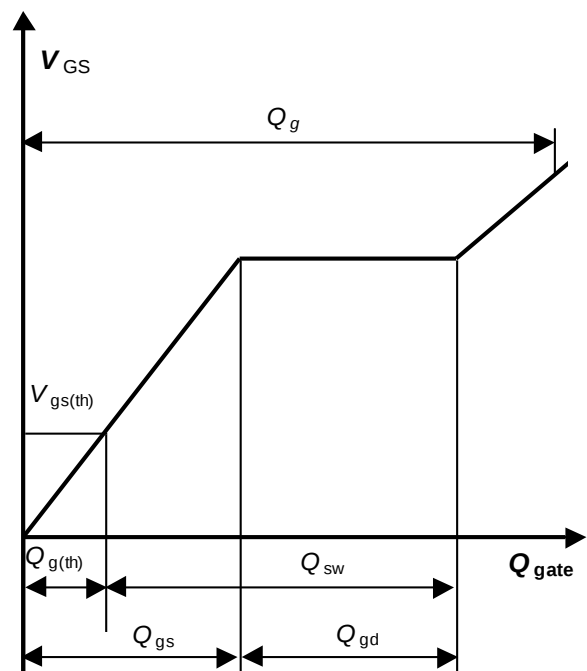


### 15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=250\ \mu\text{A}$$

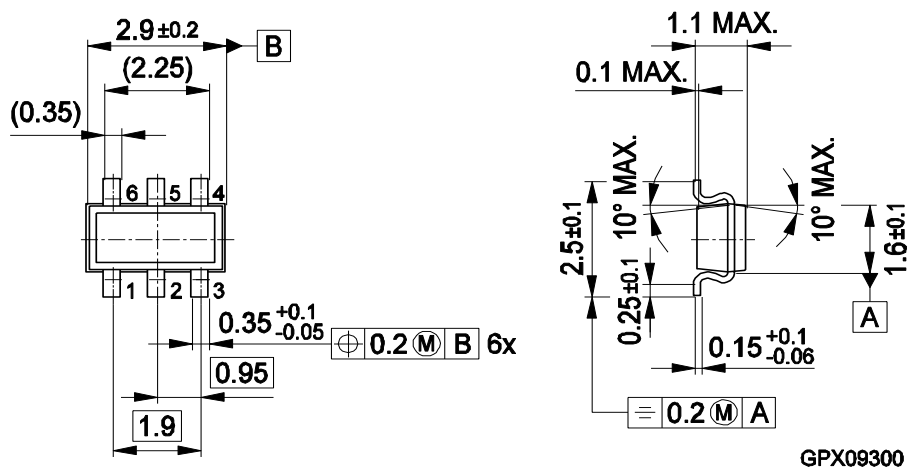


### 16 Gate charge waveforms

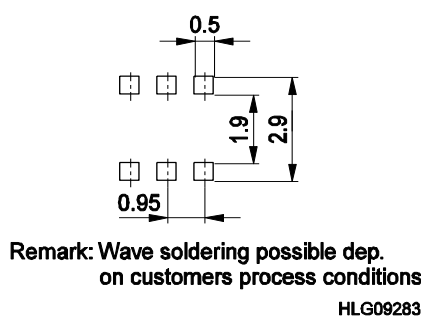


## TSOP-6

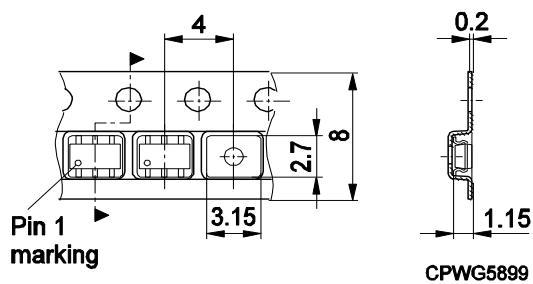
### Package Outline:



### Footprint:



### Packaging:



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